

P-Channel 30-V (D-S) MOSFET

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PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a	Q _g (Typ.)			
- 30	0.019 at V _{GS} = - 10 V	- 7.5	20 nC			
	$0.029 \text{ at V}_{GS} = -4.5 \text{ V}$	- 6.3	20110			

FEATURES

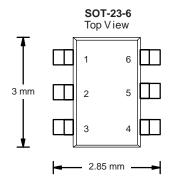
- DT-Trench Power MOSFET
- 100 % $\rm R_{\rm g}$ and UIS tested

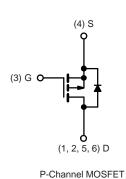
APPLICATIONS

· Load Switch



COMPLIANT





Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	- 30	V
Gate-Source Voltage		V _{GS}	± 20	V
	T _C = 25 °C		- 7.5	
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 70 °C	1 . –	- 6.3	
Continuous Dialii Current (1) = 130 C)	T _A = 25 °C	l _D	- 4.1 ^{b, c}	
	T _A = 70 °C		- 3.3 ^{b, c}	A
Pulsed Drain Current		I _{DM}	- 30	
	T _C = 25 °C		- 7.5	
Continuous Source-Drain Diode Current	T _A = 25 °C	Is	- 1.87 ^{b, c}	
Maximum Power Dissipation	T _C = 25 °C		3.5	
	T _C = 70 °C	P _D	2.2	w
	T _A = 25 °C		1.5 ^{b, c}	VV
	T _A = 70 °C		0.9 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R_{thJA}	45	55	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	34	41	- C/ VV	

Notes:

- a. Based on T_C = 25 °C.
 b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under Steady State conditions is 110 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L = 250 uA		- 31		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	l _D = - 250 μA		4.5			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	-1 -10 μΑ	
		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 7.5			Α	
	R _{DS(on)}	$V_{GS} = -10 \text{ V}, I_D = -3.0 \text{ A}$		0.019	0.027		
Drain-Source On-State Resistance ^a		$V_{GS} = -4.5 \text{ V}, I_D = -2.0 \text{ A}$		0.029	0.039	Ω	
Dynamic ^b							
Input Capacitance	C _{iss}			1450		pF	
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		180			
Reverse Transfer Capacitance	C _{rss}			153			
Total Gate Charge				20			
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3.0 \text{ A}$		4		nC	
Gate-Drain Charge	Q _{gd}			3.5			
Gate Resistance	R_g	f = 1 MHz		7		Ω	
Turn-On Delay Time	t _{d(on)}			7			
Rise Time	t _r	V_{DD} = - 15 V, R_L = 4.6 Ω		23		ns	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 3.0 A, V_{GS} = - 10 V, R_g = 1 Ω		40			
Fall Time	t _f			20			
Drain-Source Body Diode Characteristic	S						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 7.5	A	
Pulse Diode Forward Current ^a	I _{SM}				- 30		
Body Diode Voltage	V _{SD}	I _S = - 3.3 A		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			15		ns	
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = -3.0 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s, T}_J = 25 \text{ °C}$		4.7		nC	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

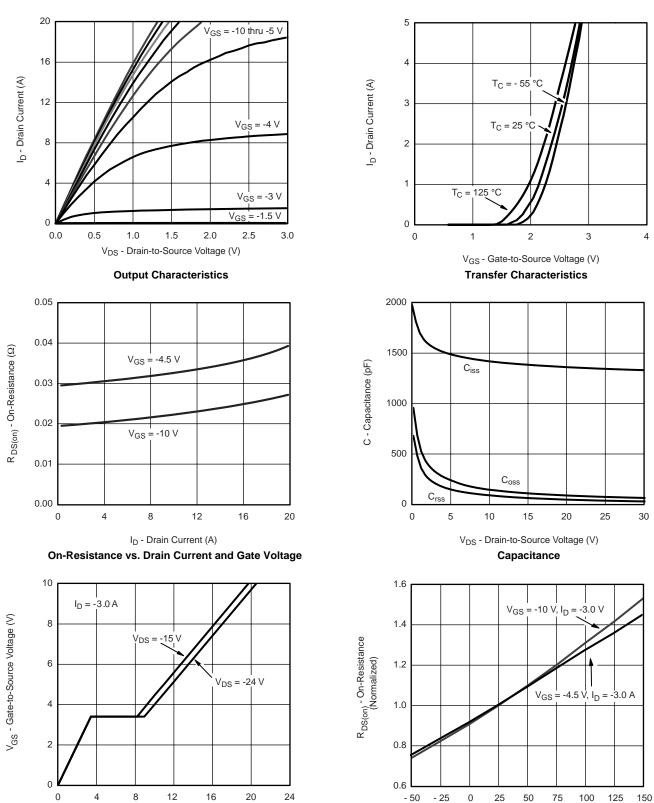
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 % b. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Q_q - Total Gate Charge (nC)

Gate Charge

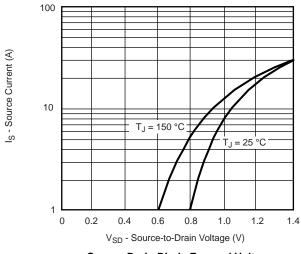


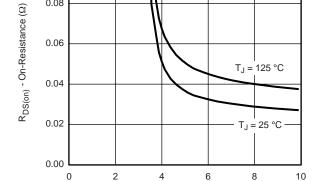
T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

 $I_D = -3.0 \text{ A}$

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

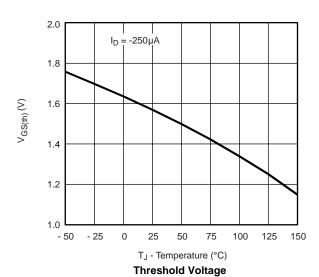




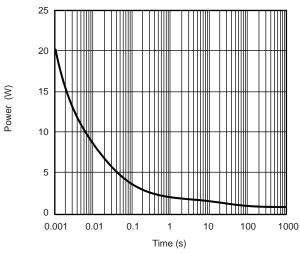
0.10

0.08

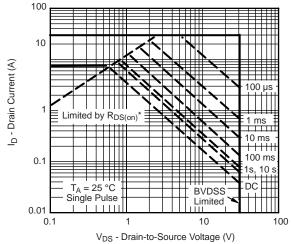
Source-Drain Diode Forward Voltage



V_{GS} - Gate-to-Source Voltage (V) On-Resistance vs. Gate-to-Source Voltage



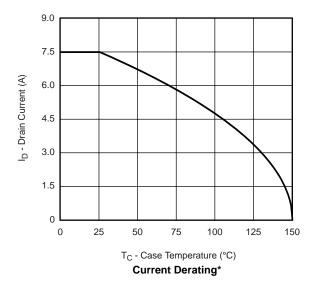
Single Pulse Power

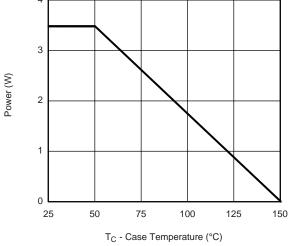


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified Safe Operating Area



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



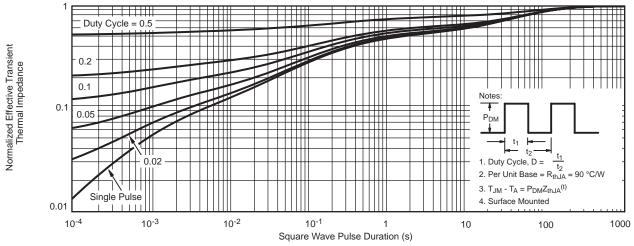


Power, Junction-to-Foot

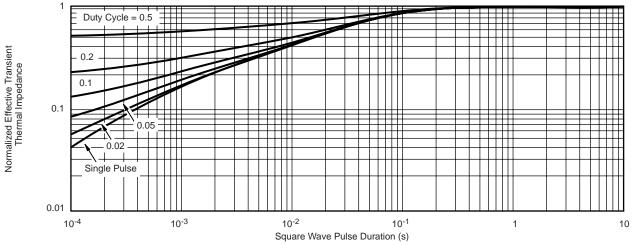
^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot





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